



National Semiconductor

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MM54HC42/MM74HC42 BCD-to-Decimal Decoder

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General Description

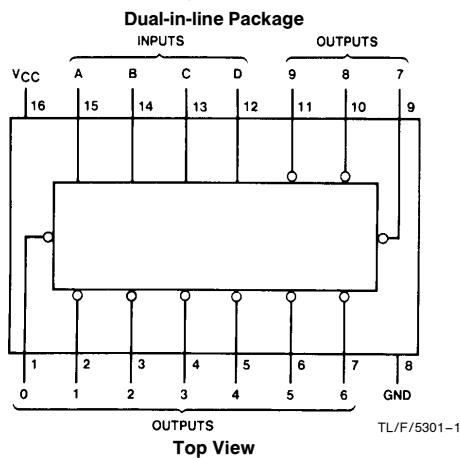
This decoder utilizes advanced silicon-gate CMOS technology. Data on the four input pins select one of the 10 outputs corresponding to the value of the BCD number on the inputs. An output will go low when selected, otherwise it remains high. If the input data is not a valid BCD number all outputs will remain high. The circuit has high noise immunity and low power consumption usually associated with CMOS circuitry, yet also has speeds comparable to low power Schottky TTL (LS-TTL) circuits, and is capable of driving 10 LS-TTL equivalent loads.

All inputs are protected from damage due to static discharge by diodes to V_{CC} and ground.

Features

- Typical propagation delay: 15 ns
 - Wide supply range: 2V–6V
 - Low quiescent current: 80 μ A (74HC)
 - Fanout of 10 LS-TTL loads

Connection Diagram

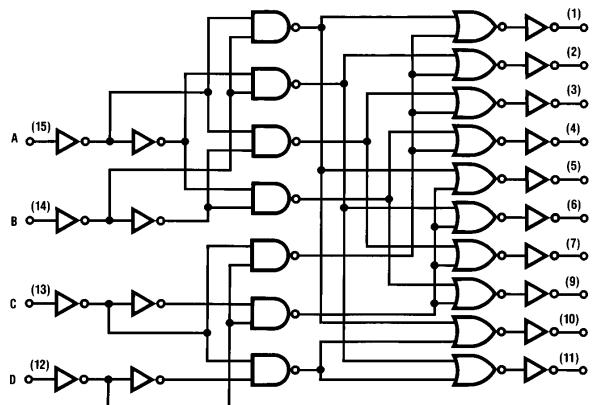


Order Number MM54HC42 or MM74HC42

Truth Table

H=High Level, L=Low Level

Logic Diagram



TL/F/5301-2

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to V_{CC} + 1.5V
DC Output Voltage (V_{OUT})	−0.5 to V_{CC} + 0.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±50 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (T_L) (Soldering 10 seconds)	260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T_A)			
MM74HC	−40	+85	°C
MM54HC	−55	+125	°C
Input Rise or Fall Times (t_r, t_f)			
$V_{CC} = 2.0V$	1000	ns	
$V_{CC} = 4.5V$	500	ns	
$V_{CC} = 6.0V$	400	ns	

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
				Typ		$T_A = -40 \text{ to } 85^\circ C$	$T_A = -55 \text{ to } 125^\circ C$	
V_{IH}	Minimum High Level Input Voltage		2.0V 4.5V 6.0V	1.5 3.15 4.2		1.5 3.15 4.2	1.5 3.15 4.2	V
V_{IL}	Maximum Low Level Input Voltage**		2.0V 4.5V 6.0V	0.5 1.35 1.8		0.5 1.35 1.8	0.5 1.35 1.8	V
V_{OH}	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 20 \mu A$	2.0V 4.5V 6.0V	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 4.0 \text{ mA}$ $ I_{OUT} \leq 5.2 \text{ mA}$	4.5V 6.0V	4.2 5.7	3.98 5.48	3.84 5.34	3.7 5.2	V
V_{OL}	Minimum Low Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 20 \mu A$	2.0V 4.5V 6.0V	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 4.0 \text{ mA}$ $ I_{OUT} \leq 5.2 \text{ mA}$	4.5V 6.0V	0.2 0.2	0.26 0.26	0.33 0.33	0.4 0.4	V
I_{IN}	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		8.0	80	160	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C; ceramic "J" package: −12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V ± 10% the worst case output voltages (V_{OH} , and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at $V_{CC} = 5.5V$ and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} , and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

** V_{IL} limits are currently tested at 20% of V_{CC} . The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $V_{CC} = 5V$, $T_A = 25^\circ C$, $C_L = 15 \text{ pF}$, $t_r = t_f = 6 \text{ ns}$

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay		15	25	ns

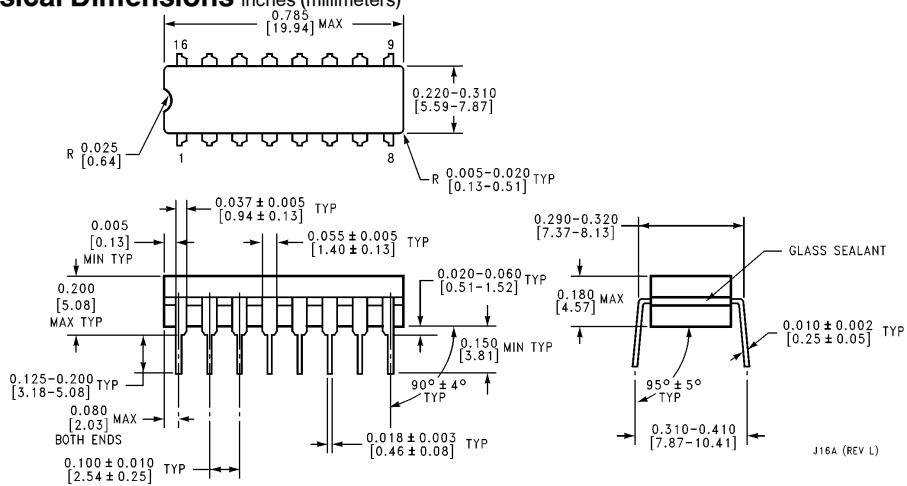
AC Electrical Characteristics $V_{CC} = 2.0V \text{ to } 6.0V$, $C_L = 50 \text{ pF}$, $t_r = t_f = 6 \text{ ns}$ (unless otherwise specified)

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
				Typ	Guaranteed Limits			
t_{PHL}, t_{PLH}	Maximum Propagation Delay		2.0V	75	150	189	224	ns
			4.5V	17	30	38	45	
			6.0V	15	26	32	38	
t_{TLH}, t_{THL}	Maximum Output Rise and Fall Time		2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	
			6.0V	7	13	16	19	
C_{PD}	Power Dissipation Capacitance (Note 5)	(per package)		62				pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF

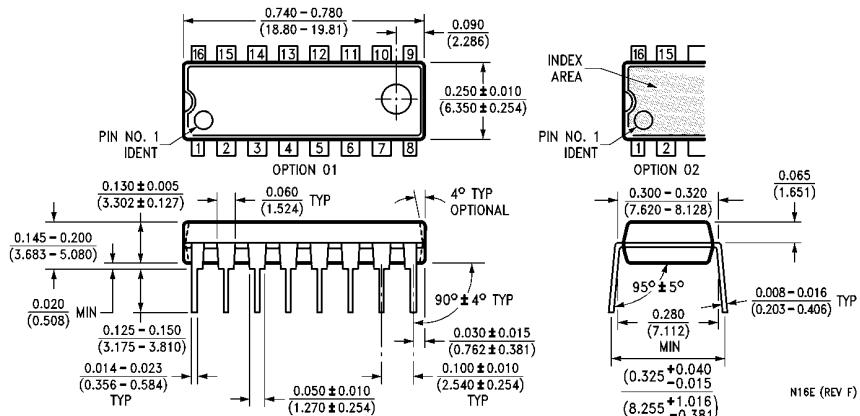
Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

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Physical Dimensions inches (millimeters)



Order Number MM54HC42J or MM54HC42J
NS Package J16A



Order Number MM54HC42N
NS Package N16E

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